KEL®

BAV99

SWITCHING DIODE 開關二極管(BAV99)

■FEATURES 特點

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Power dissipation 耗散功率	P_D(Ta=25℃)	225	mW
Forward Current 正向電流	I_F	200	mA
Reverse Voltage 反向電壓	V_R	70	V
Junction and Storage Temperature 結溫和儲藏溫度	T_J,T_{stg}	-55to+150℃	

■DEVICE MARKING 打標

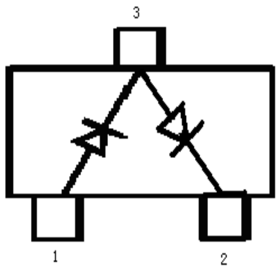
BAV99=A7

■ELECTRICAL CHARACTERISTICS 電特性

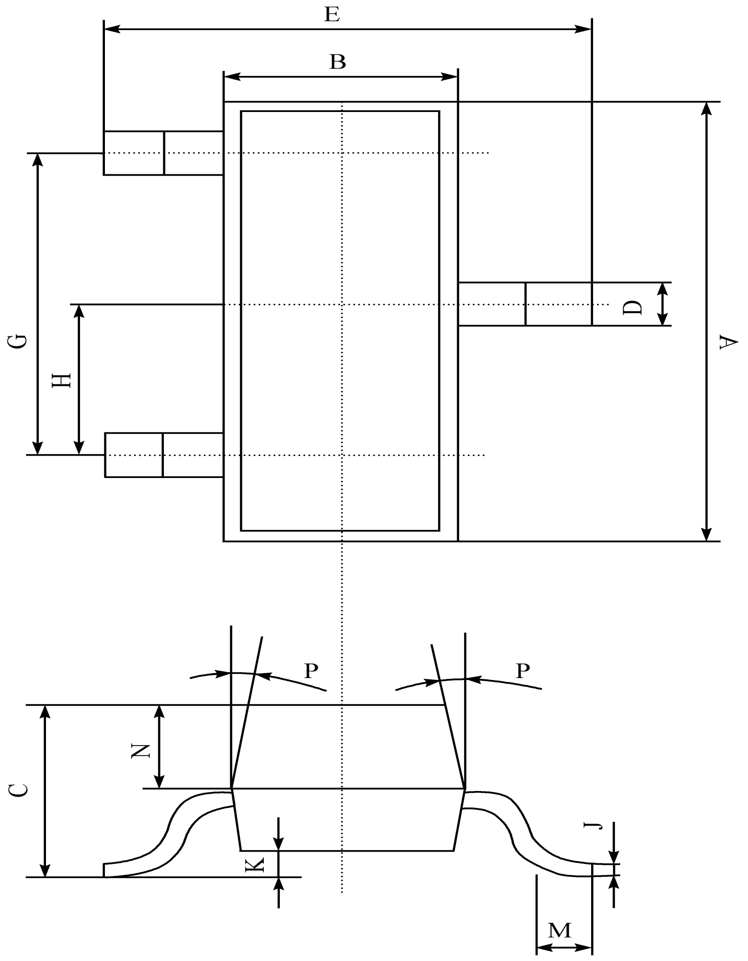
(T_A=25℃ unless otherwise noted 如無特殊说明，溫度爲 25℃)

Characteristic 特性參數	Symbol 符號	Min 最小值	Max 最大值	Unit 單位
Reverse Breakdown Voltage 反向擊穿電壓 (I_R=100uA)	$V_{(BR)}$	70	—	V
Reverse Leakage Current 反向漏電流 (V_R=70V)	I_R	—	1	uA
Forward Voltage(Test Condition)正向電壓 I_F=1mA I_F=10mA I_F=50mA I_F=150mA	V_F	—	715 855 1000 1250	mV
Diode Capacitance 二極體電容 (V_R=0V, f=1MHz)	C_D	—	1.5	pF
Reverse Recovery Time 反向恢復時間	T_{rr}	—	6	nS

■SOT-23 内部结构



■DIMENSION 外形封裝尺寸



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00–0.10
M	⩾0.2
N	0.60±0.10
P	7±2°

This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website http://www.takcheong.com.

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